

# High-Voltage, High-Current Darlington Arrays

**THESE HIGH-VOLTAGE, HIGH-CURRENT**

Darlington arrays are comprised of seven silicon NPN darlington pairs on a common monolithic substrate. All units have open-collector outputs and integral diodes for inductive load transient suppression.

ULN2003 has a 2.7 kΩ series base resistor for each darlington pair, allowing operation directly with TTL or CMOS operating at a supply voltage of 5V. These devices will handle numerous interface needs particularly those beyond the capabilities of standard logic buffers.

ULN2004 has a 10.5 kΩ series input resistor that

permits operation directly from CMOS or PMOS outputs utilizing supply voltages of 6 to 15 V.

ULN2003/ULN2004 is the original high-voltage, high-current darlington array. The output transistors are capable of sinking 500 mA and will sustain at least 50V in the off state. Output may be paralleled for higher load-current capability.

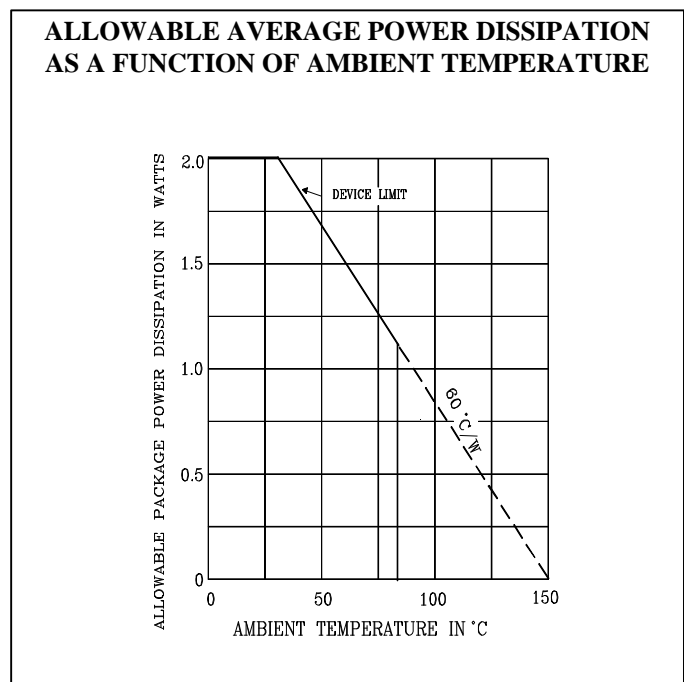
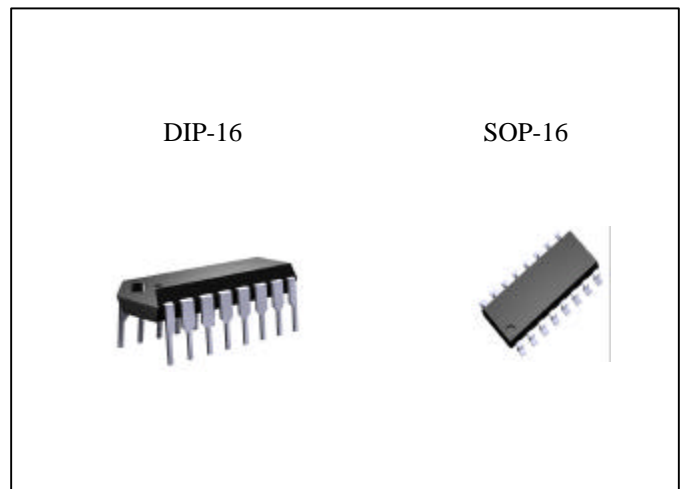
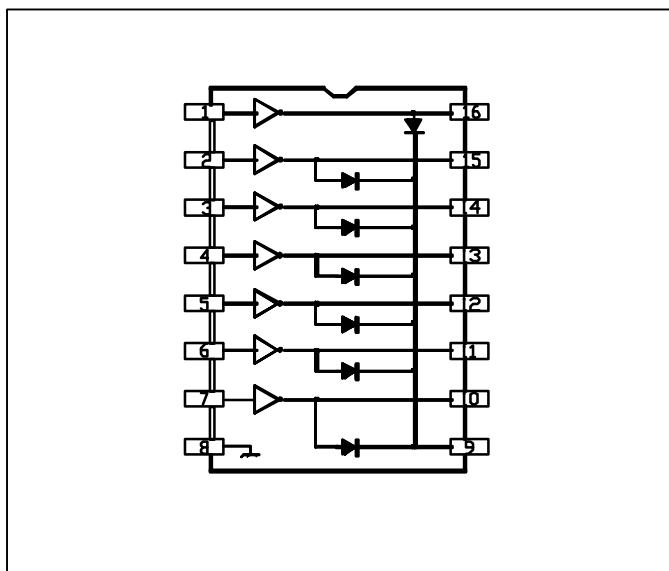
ULN2003/ULN2004 darlington arrays are furnished in a 16-Pin dual in-line plastic package. These can also be supplied in a hermetic dual in-line package for use in military and aerospace applications.

**DEVICE NUMBER DESIGNATION**

VCE(MAX)	50V
IC(MAX)	500mA
Logic	Type Number
5V TTL, CMOS	ULN2003
6-15V CMOS,PMOS	ULN2004

**ORDER INFORMATION**

Device	Operation Temperature	Package
ULN2003CD	- 20°C to + 85°C	DIP-16
ULN2004CD		DIP-16
ULN2003CS	- 20°C to + 85°C	SOP-16
ULN2004CS		SOP-16



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**ABSOLUTE MAXIMUM RATINGS**

at +25 °C Free - Air Temperature  
( unless otherwise noted )

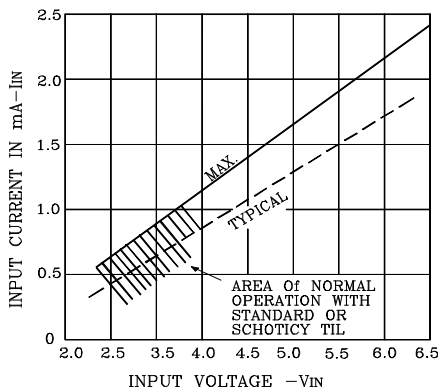
- Input Voltage,  $V_{IN}$  (ULN2003, ULN2004) ..... 30 V
- Continuous Input Current,  $I_{IN}$  ..... 25 mA
- Power Dissipation,  $P_D$  ( one Darlington pair ) ..... 1.0 W  
( total package ) ..... 2.0 W\*
- Operating Ambient Temperature Range,  $T_A$  ..... -20°C to + 85°C
- Storage Temperature Range,  $T_S$  ..... - 55°C to + 150°C

\*Debate at the rate of 16.67 mW/°C above + 25°C. ,,

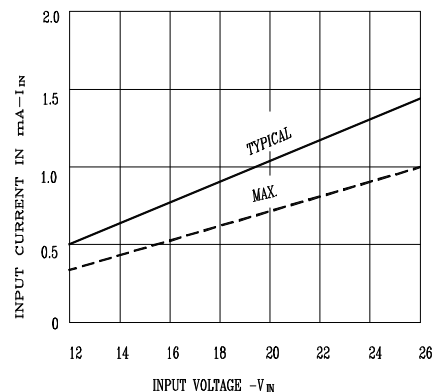
Under normal operating conditions, these devices will sustain 350 mA per output with  $V_{CE(STA)} = 1.6 V$  at +70°C with a pulse width of 20 ms and a duty cycle of 34%.

**PARTIAL SCHEMATICS**

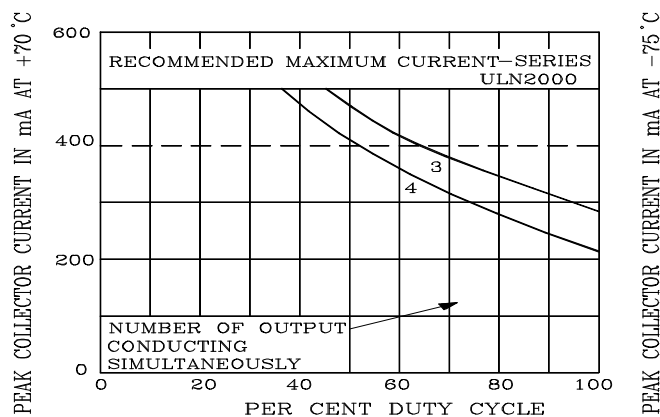
Series ULN2003  
(each driver)



Series ULN2004  
(each driver)



**PEAK COLLECTOR CURRENT AS A FUNCTION OF DUTY CYCLE**

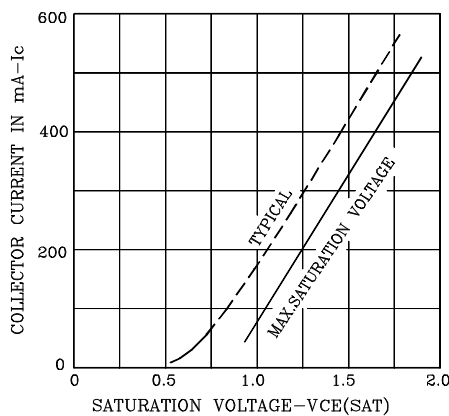


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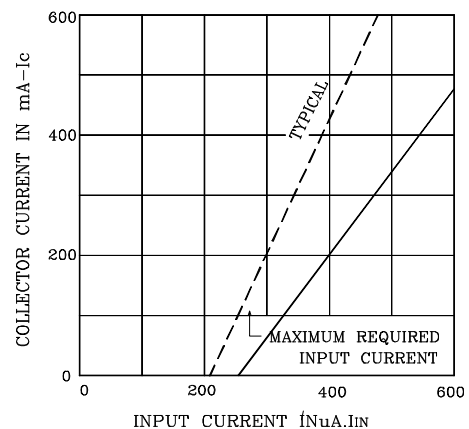
**ELECTRICAL CHARACTERISTICS AT +25°C ( unless otherwise noted )**

Characteristic	Symbol	Test Fig.	Applicable Devices	Test Conditions	Limits			
					Min.	Typ.	Max.	Units
Output Leakage Current	I <sub>CEX</sub>	1A	All	V <sub>CE</sub> =50V, T <sub>A</sub> =25°C	--	--	50	μA
				V <sub>CE</sub> =50V, T <sub>A</sub> =70°C	--	--	100	μA
		1B	ULN2004	V <sub>CE</sub> =50V, T <sub>A</sub> =70°C°, V <sub>IN</sub> =1.0V	--	--	500	μA
Collector - Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	2	All	I <sub>C</sub> =100mA, I <sub>S</sub> =250μA	--	0.9	1.1	V
				I <sub>C</sub> =200mA, I <sub>S</sub> =350μA	--	1.1	1.3	V
				I <sub>C</sub> =350mA, I <sub>S</sub> =500μA	--	1.3	1.6	V
Input Current	I <sub>IN(ON)</sub>	3	ULN2003	V <sub>IN</sub> =3.85V	--	0.93	1.35	mA
			ULN2004	V <sub>IN</sub> =5.0V	--	0.35	0.5	mA
				V <sub>IN</sub> =12V	--	1.0	1.45	mA
Input Voltage	I <sub>IN(OFF)</sub>	4	All	I <sub>C</sub> =500μA, T <sub>A</sub> =70°C	50	65	--	μA
				ULN2003	V <sub>CE</sub> =2.0V, I <sub>C</sub> =200mA	--	--	2.4
	V <sub>CE</sub> =2.0V, I <sub>C</sub> =250mA	--	--		2.7	V		
	V <sub>CE</sub> =2.0V, I <sub>C</sub> =300mA	--	--		3.0	V		
	V <sub>IN(ON)</sub>	5	ULN2004	V <sub>CE</sub> =2.0V, I <sub>C</sub> =125mA	--	--	5.0	V
				V <sub>CE</sub> =2.0V, I <sub>C</sub> =200mA	--	--	6.0	V
				V <sub>CE</sub> =2.0V, I <sub>C</sub> =275mA	--	--	7.0	V
V <sub>CE</sub> =2.0V, I <sub>C</sub> =350mA	--	--	8.0	V				
Input Capacitance	C <sub>IN</sub>	--	All		--	15	25	pF
Turn-On Delay	t <sub>PLH</sub>	--	All	0.5 E <sub>in</sub> to 0.5 E <sub>out</sub>	--	0.25	1.0	μS
Turn-Off Delay	t <sub>PHL</sub>	--	All	0.5 E <sub>in</sub> to 0.5 E <sub>out</sub>	--	0.25	1.0	μS
Clamp Diode Leakage Current	I <sub>R</sub>	6	All	V <sub>R</sub> =50V, T <sub>A</sub> =25°C	--	--	50	μA
				V <sub>R</sub> =50V, T <sub>A</sub> =70°C	--	--	100	μA
Clamp Diode Forward Voltage	V <sub>F</sub>	7	All	I <sub>F</sub> =350mA	--	1.7	2.0	V

COLLECTOR CURRENT AS A FUNCTION OF SATURATION VOLTAGE



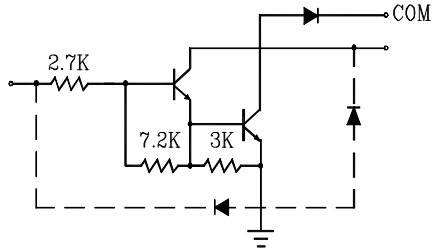
COLLECTOR CURRENT AS A FUNCTION OF INPUT CURRENT



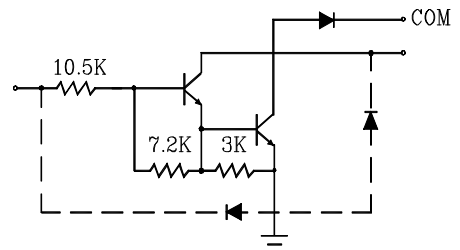
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INPUT CURRENT AS A FUNCTION OF INPUT VOLTAGE

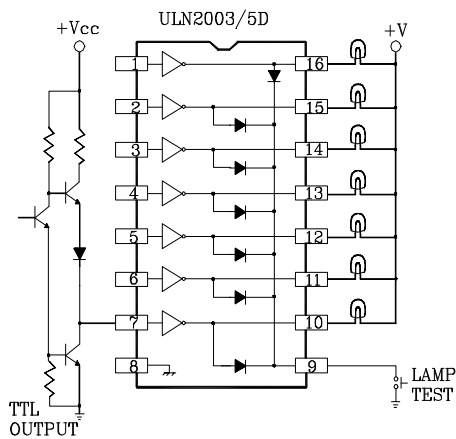
SERIES ULN2003



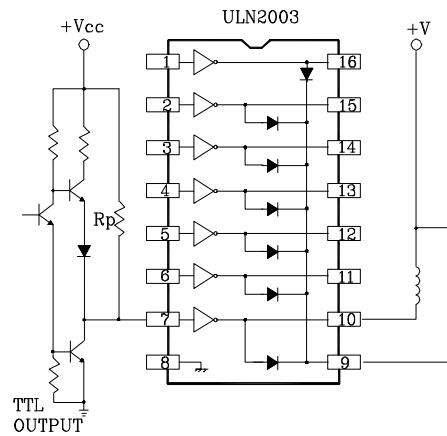
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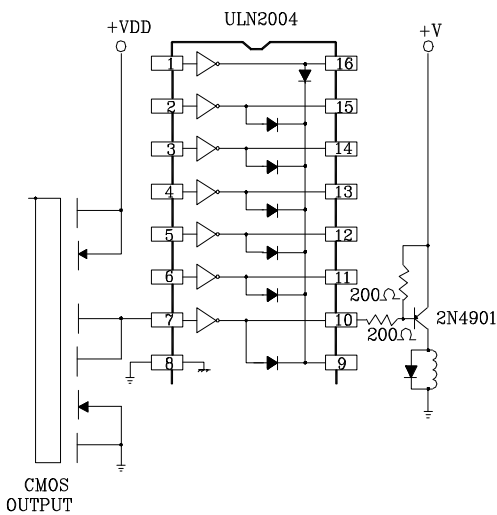
TTL TO LOAD



USE OF PULL-UP RESISTORS TO INCREASE DRIVE CURRENT



BUFFER FOR HIGH-CURRENT LOAD



TEST FIGURES

FIGURE 1A

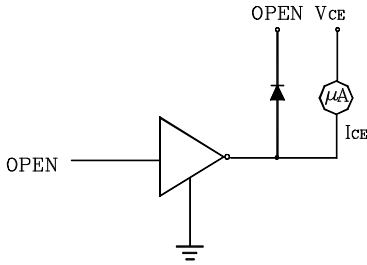


FIGURE 4

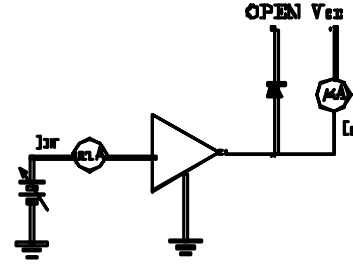


FIGURE 1B

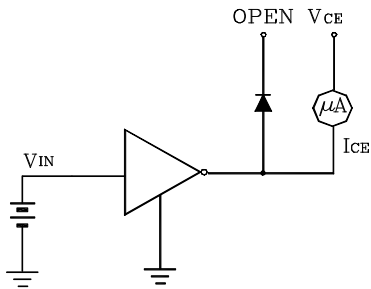


FIGURE 5

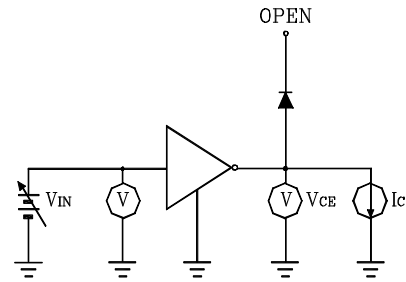


FIGURE 2

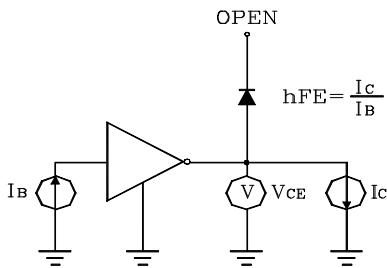


FIGURE 6

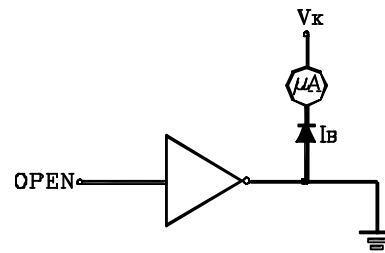


FIGURE 3

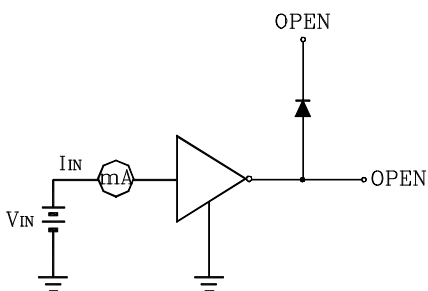


FIGURE 7

